a magnetic field generator configured to apply a magnetic field to a surface of the substrate to which the plasma process is applied; and

an auxiliary electrode provided on an outer periphery of said first electrode to excite plasma in a vicinity of the auxiliary electrode,

wherein electrons in the plasma drift from a front surface of said auxiliary electrode to a back surface thereof and from the back surface of said auxiliary electrode to the front surface thereof.

- 2. (Amended) The plasma processing apparatus as claimed in claim 1, wherein the front surface of said auxiliary electrode is covered by an insulating material.
- 3. (Amended) The plasma processing apparatus as claimed in claim 1 or 2, wherein the substrate has a surface positioned at a level substantially equal to a level of the front surface of said auxiliary electrode.
  - 4. (Amended) The plasma processing apparatus as claimed in claim 1 or 2, wherein said magnetic field generator comprises a dipole ring-magnet.
  - 5. (Amended) The plasma processing apparatus as claimed in claim 1 or 2, wherein said first electrode is supplied with a first radio frequency and said auxiliary electrode is supplied with a second radio frequency and wherein the first and the second radio frequencies are equal to each other and have different phases thereof are different from each other.

- 6. (Amended) The plasma processing apparatus as claimed in claim 1 or 2, wherein said first electrode is supplied with a first radio frequency and said auxiliary electrode is supplied with a second radio frequency and wherein said second radio frequency is higher than said first radio frequency.
- 7. (Amended) A plasma processing method performed in a plasma processing apparatus comprising a first electrode on which a substrate on which a substrate is positioned and an auxiliary electrode provided on an outer periphery of said first electrode, the method comprising:

subjecting the substrate to a plasma process containing a plasma;

applying a magnetic field to a surface of the substrate to which the plasma process is applied;

exciting plasma on at least a back surface of the auxiliary electrode; and causing electrons in the plasma to drift from a front surface of said auxiliary electrode to the back surface thereof and from the back surface of said auxiliary electrode to the front surface thereof.